



## SILICON CONTROLLED RECTIFIERS

### 175/235RK SERIES

### Power Silicon Controlled Rectifiers

Types : 175RK20 TO 175RK160, 235RK20 TO 235RK160

#### FEATURES

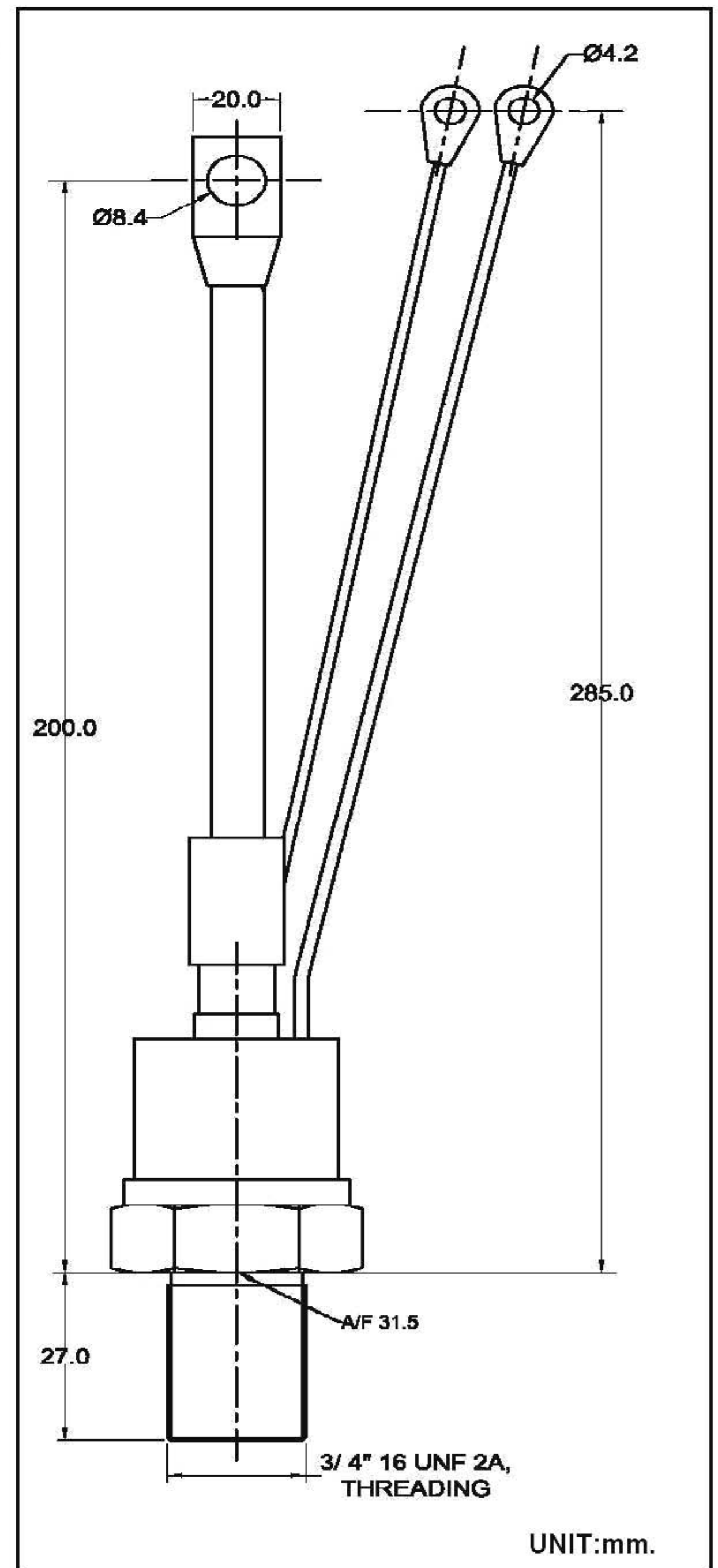
- ❖ Centre amplifying gate.
- ❖ International standard case TO-209AB (TO-93).
- ❖ Threaded studs UNF 3/4 - 16UNF2A.
- ❖ Compression Bonded Encapsulation for heavy duty operations such as severe thermal cycling.

#### TYPICAL APPLICATIONS

- ❖ DC motor control (e.g. for Machine tools).
- ❖ Controlled rectifiers (e.g. for Battery Charging, Uninterrupted Power Supply).
- ❖ AC controllers (e.g. Temperature control, Lights control).

#### MAJOR RATINGS & CHARACTERISTICS

Parameters	175RK	235RK	Units
$I_{T(AV)}$	170	230	A
@ $T_c$	85		°C
$I_{T(RMS)}$	270	361	A
$I_{TSM}$ @ 50 Hz	3900	4800	A
$I^2t$ @ 50 Hz	105	163	KA <sup>2</sup> s
$V_{DRM} / V_{RRM}$	200 to 1600		V
$t_q$ typical	100		μs
$T_J$	-40 to 125		°C



# SILICON CONTROLLED RECTIFIERS

## 175/235RK SERIES

### ELECTRICAL SPECIFICATION VOLTAGE RATINGS

Type Number	Voltage Code	$V_{RRM} / V_{DRM}$ max. repetitive peak and off-state voltage V	$V_{RSM}$ max. non-repetitive peak voltage V	$I_{DRM} / I_{RRM}$ max. @ 125°C mA
175RK/235RK	20	200	300	30
	40	400	500	
	60	600	700	
	80	800	900	
	100	1000	1100	
	120	1200	1300	
	140	1400	1500	
	160	1600	1700	

### ON-STATE CONDUCTION

Parameter	175RK	235RK	Units	Conditions
$I_{T(AV)}$	170	230	A	180°C conduction, half sine wave
	85		°C	
$I_{T(RMS)}$	270	361		
$I_{TSM}$	3900	4800	A	t = 10ms Sinusoidal half wave, Initial $T_J = T_J$ max.
$I^2t$	76	115	kA <sup>2</sup> s	t = 10ms
$V_{T(TO)}$	1.08	0.92	V	$T_J = T_J$ max.
$r_{\theta}$	1.8	0.81	mΩ	$T_J = T_J$ max.
$V_{TM}$	1.75	1.55	V	$I_{pk} = \pi \times I_{T(AV)}$ , $T_J = 125^\circ\text{C}$ , $t_p = 10\text{ms}$ sine pulse
$I_H$	300		mA	$T_J = 25^\circ\text{C}$ , anode supply 12V resistive load
$I_L$	600			

### SWITCHING

Parameter	175RK/235RK	Units	Conditions
di/dt	100	A/μs	Gate drive 20V, 20Ω, $t_r \leq 1\ \mu\text{s}$ $T_J = 125^\circ\text{C}$ , anode voltage $\leq 80\% V_{DRM}$
$t_d$	1.0	μs	Gate current 1A, $di_g/dt = 1\text{A}/\mu\text{s}$ $V_d = 0.67\% V_{DRM}$ , $T_J = 25^\circ\text{C}$
$t_q$	100		$I_{TM} = 300\text{A}$ , $T_J = 125^\circ\text{C}$ , $di/dt = 20\text{A}/\mu\text{s}$ , $V_R = 50\text{V}$ $dv/dt = 20\text{V}/\mu\text{s}$ , Gate 0V 100Ω, $t_p = 500\mu\text{s}$

# SILICON CONTROLLED RECTIFIERS

## 175/235RK SERIES

### BLOCKING

	Parameter	175RK/235RK	Units	Conditions
dv/dt	Maximum critical rate of rise of off-state voltage	500	V/ $\mu$ s	$T_J = 125^\circ\text{C}$ , linear to 80% rated $V_{\text{DRM}}$
$I_{\text{RRM}}$ $I_{\text{DRM}}$	Max. peak reverse and off-state leakage current	30	mA	$T_J = 125^\circ\text{C}$ , rated $V_{\text{DRM}}/V_{\text{DRM}}$ applied

### TRIGGERING

	Parameter	175RK/235RK		Units	Conditions
$P_{\text{GM}}$	Maximum peak gate power	10.0		W	$T_J = 125^\circ\text{C}$ , $t_p \leq 5\text{ms}$
$P_{\text{G(AV)}}$	Maximum average gate power	2.0			$T_J = 125^\circ\text{C}$ , $f = 50\text{Hz}$ , $d\% = 50$
$I_{\text{GM}}$	Max. peak positive gate current	3.0		A	$T_J = 125^\circ\text{C}$ , $t_p \leq 5\text{ms}$
$+V_{\text{GM}}$	Max. peak positive gate voltage	20		V	$T_J = 125^\circ\text{C}$ , $t_p \leq 5\text{ms}$
$-V_{\text{GM}}$	Max. peak negative gate voltage	5.0			
$I_{\text{GT}}$	DC gate current required to trigger	TYP.	MAX.	mA	$T_J = 25^\circ\text{C}$ Max. required gate trigger / current / voltage are the lowest value which will trigger all units 12V anode-to-cathode applied.
		90	150		
$V_{\text{GT}}$	DC gate voltage required to trigger	1.8	3.0	V	$T_J = 25^\circ\text{C}$
$I_{\text{GD}}$	DC gate current not to trigger	10		mA	$T_J = 125^\circ\text{C}$ Max. gate current / voltage not to trigger is the max. value which will not trigger any unit with rated $V_{\text{DRM}}$ anode-to-cathode applied.
$V_{\text{GD}}$	DC gate voltage not to trigger	0.25			

### THERMAL AND MECHANICAL SPECIFICATION

	Parameter	175RK/235RK		Units	Conditions
$T_J$	Max. operating temperature range	-40 to 125		$^\circ\text{C}$	
$T_{\text{stg}}$	Max. storage temperature range	-40 to 150			
$R_{\text{thJC}}$	Max. thermal resistance, junction to case	0.105	0.10	K/W	DC operation
$R_{\text{thCS}}$	Max. thermal resistance, case to heat sink	0.04			Mounting surface, smooth, flat and greased
F	Mounting force, $\pm 10\%$	31		Nm	Non lubricated threads
wt	Approximate weight	280		gm	
	Case style	To - 209AE (TO-118)			See outline

# SILICON CONTROLLED RECTIFIERS

---

## ORDER INFORMATION TABLE

175/235	RK	40	M
---------	----	----	---

①                      ②                      ③                      ④

- ① - Current Code
- ② - RK - Essential part number
- ③ - Voltage Rating (See table)
- ④ - None - Stud 3/4" 16UNF 2A Threading  
M - Stud M20 x 1.5P Metric Threading

# SILICON CONTROLLED RECTIFIERS

## 175/235RK SERIES

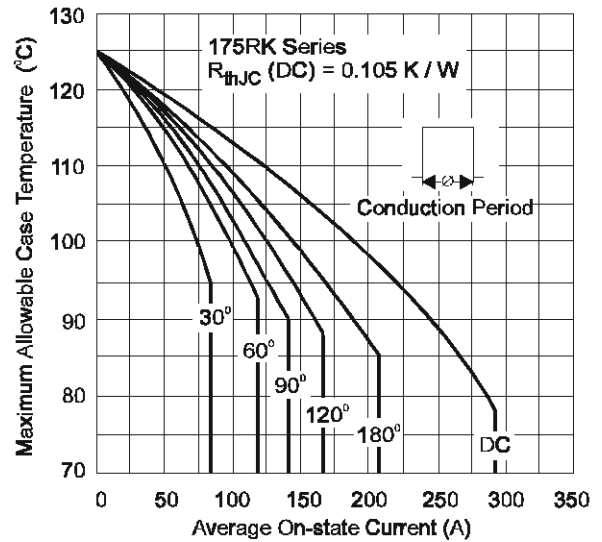
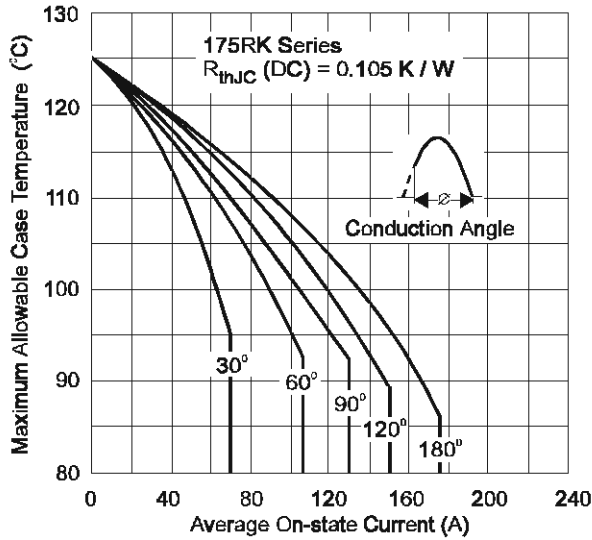


Fig. 1 - Current Ratings Characteristics

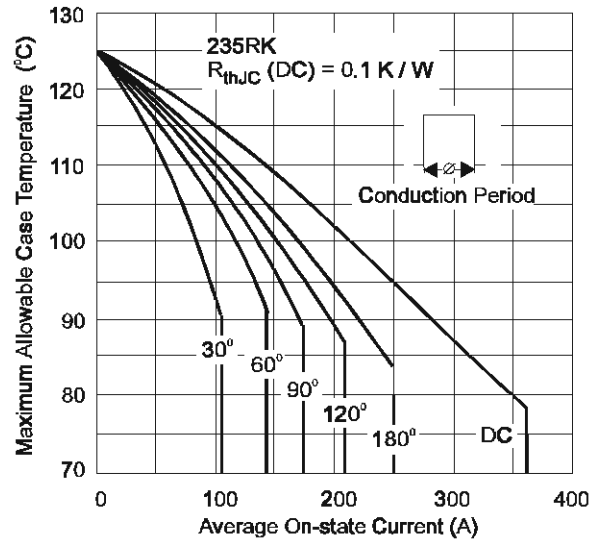
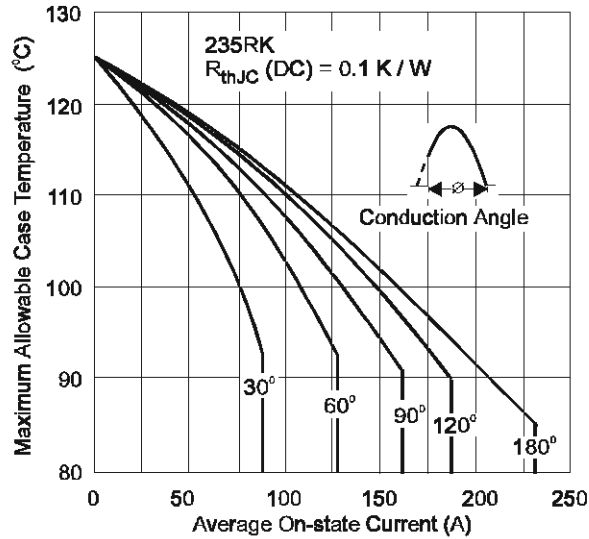


Fig. 2 - Current Ratings Characteristics

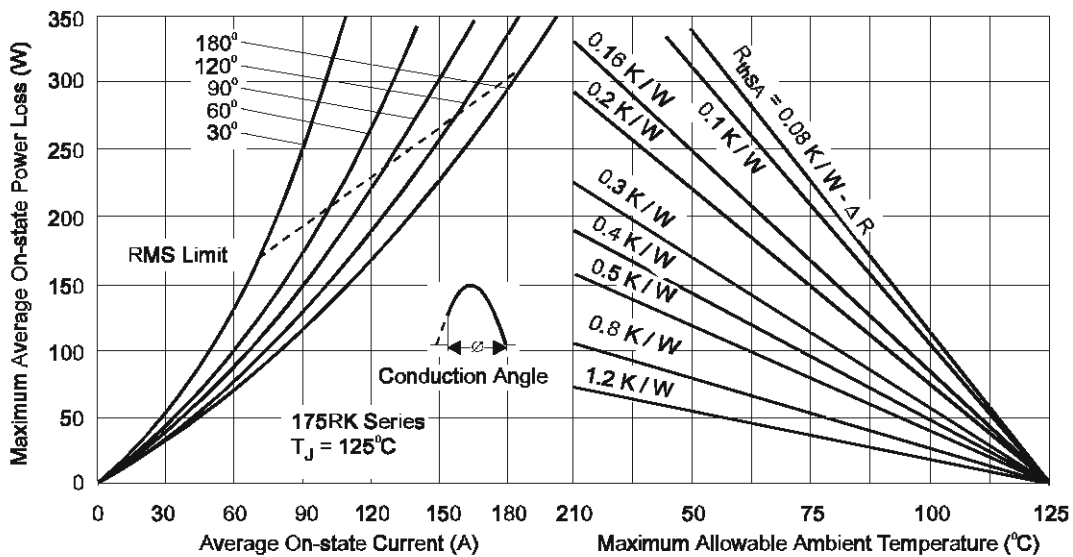


Fig. 3 - On-state Power Loss Characteristics

# SILICON CONTROLLED RECTIFIERS

## 175 / 235RK SERIES

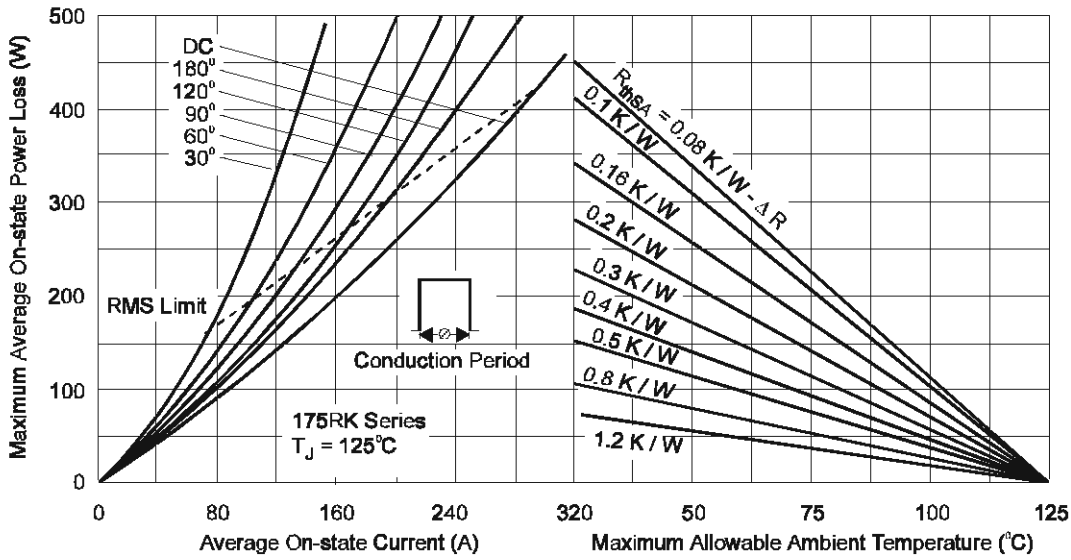


Fig. 4 - On-state Power Loss Characteristics

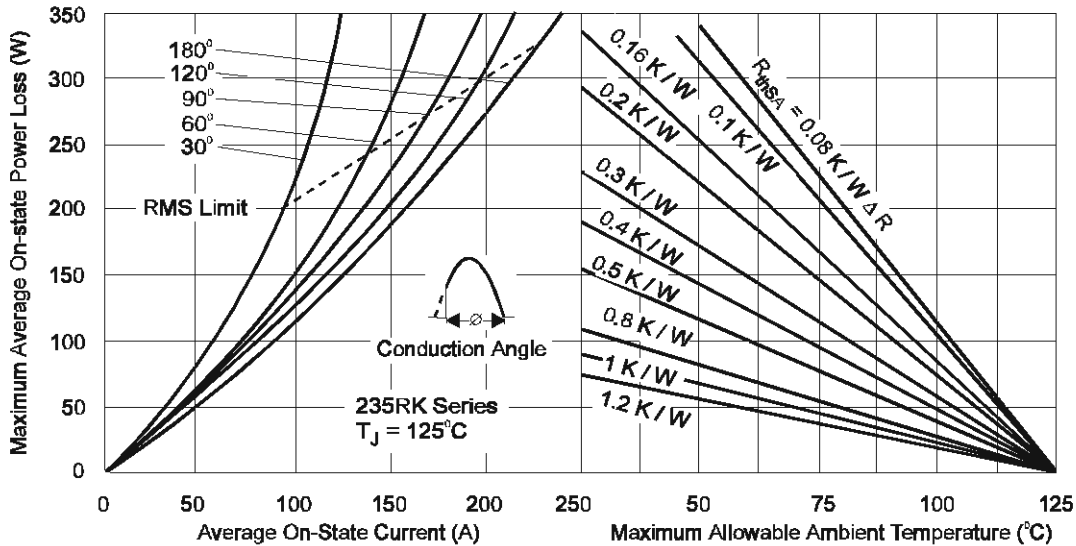


Fig. 5 - On-state Power Loss Characteristics

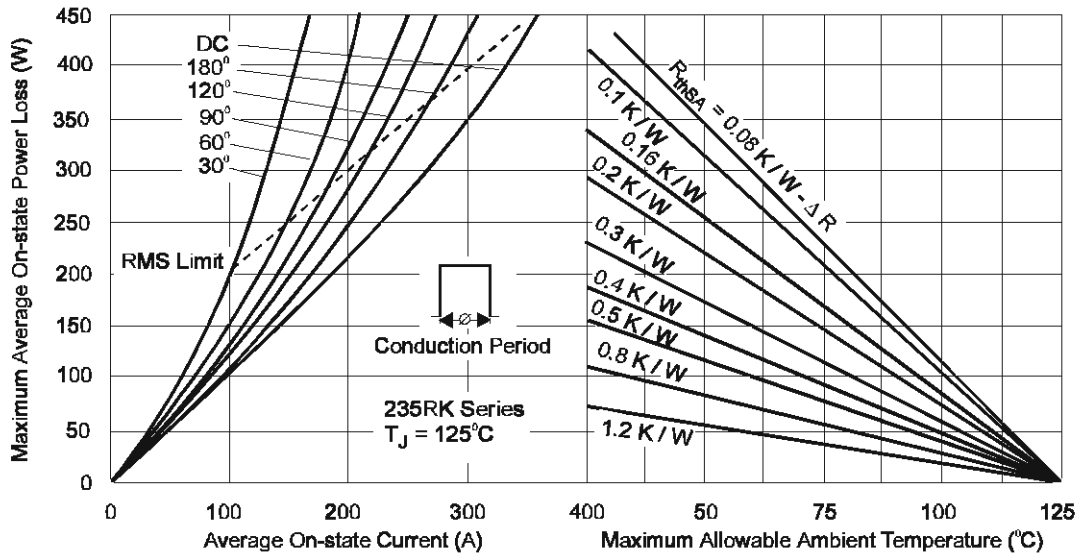
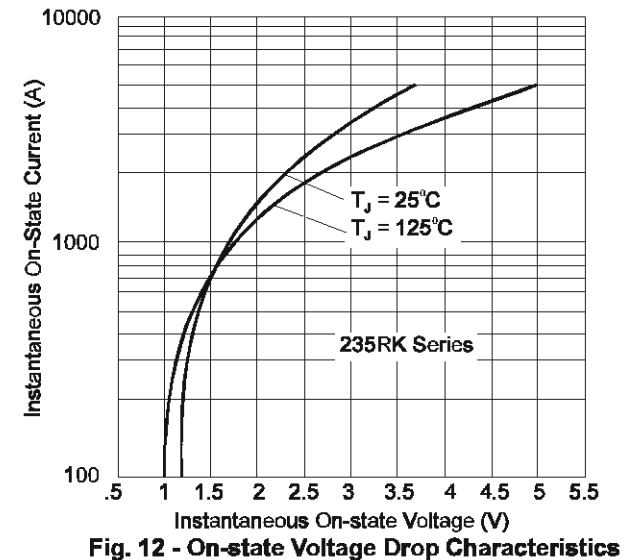
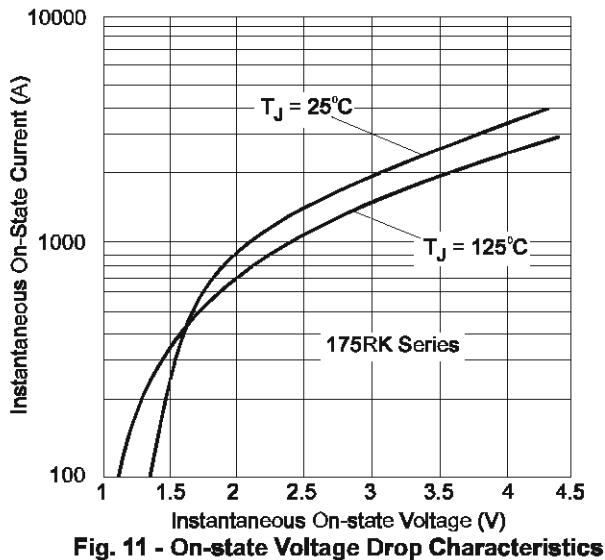
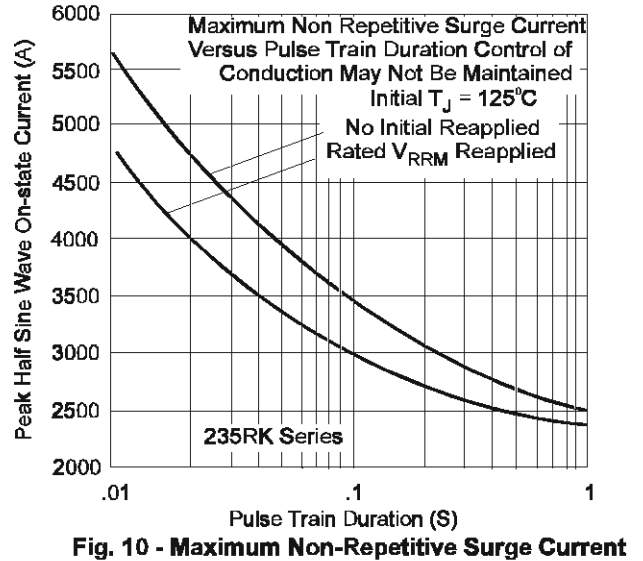
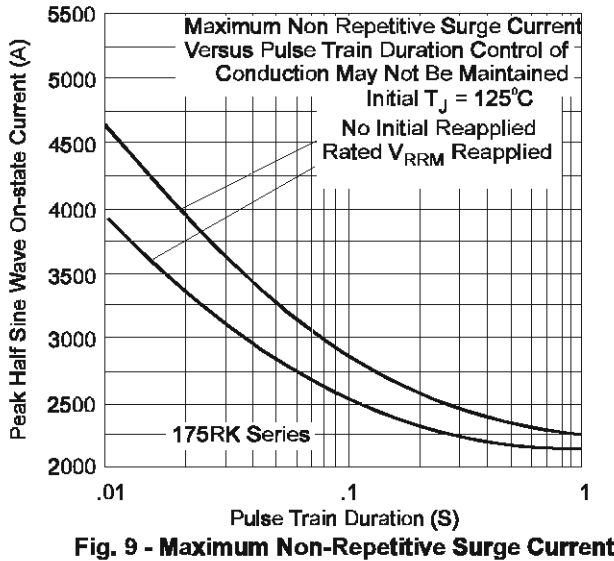
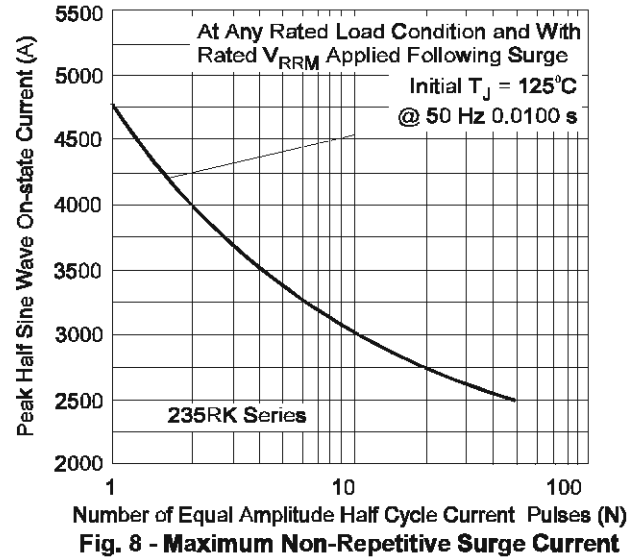
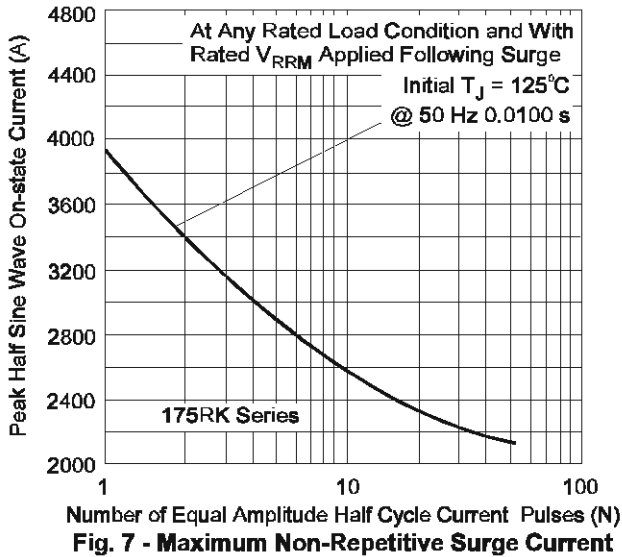


Fig. 6 - On-state Power Loss Characteristics

# SILICON CONTROLLED RECTIFIERS

## 175/235RK SERIES



# SILICON CONTROLLED RECTIFIERS

## 175 / 235RK SERIES

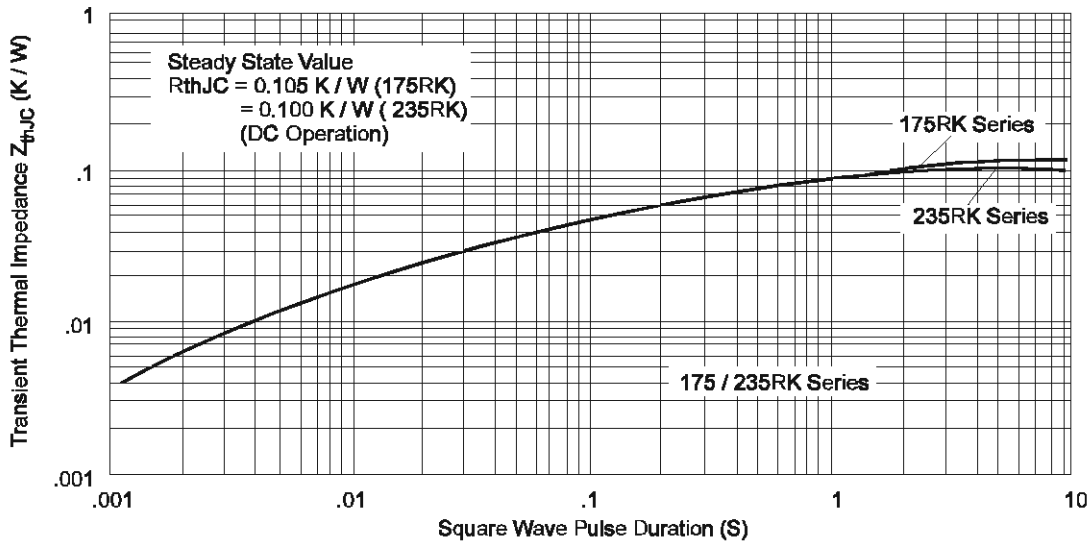


Fig. 13 - Thermal Impedance  $Z_{thJC}$  Characteristics

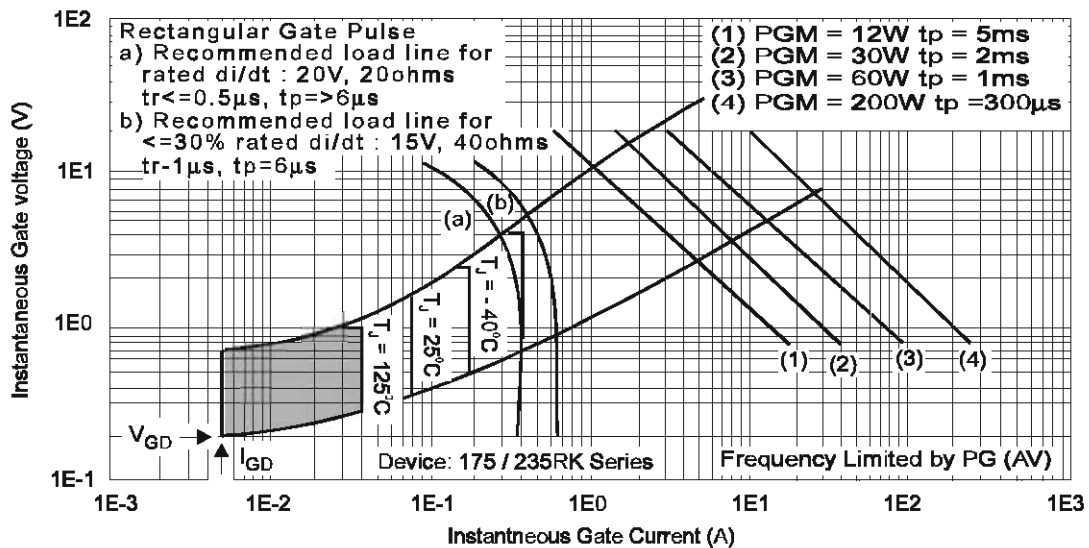


Fig. 9 - Gate Characteristics